

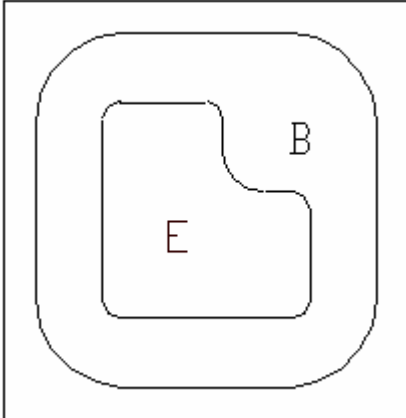
A1015 Silicon PNP Epitaxial Transistor

Description: The A1015 is designed for audio frequency general purpose amplifier applications and driver stage amplifier applications

Features: ●Excellent h_{FE} Linearity

●Complementary to C1815

Chip Appearance

	Chip Size		350um × 350um
	Chip Thickness		210 ± 20um
	Bonding Pad Size	Base	110um × 110um
		Emitter	100um × 100um
	Front Metal		Al
	Backside Metal		Au(As)
	Scribe line width		40um
	Wafer Size		6 inch

Electrical Characteristics(Ta=25°C)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=-60V, I_E=0$		-0.1	uA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=-5V, I_C=0$		-0.1	uA
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C=-0.1mA,$	-60		V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=-1mA,$	-50		V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E=-0.1mA,$	-5.0		V
DC Current Gain	h_{FE}	$V_{CE}=-6V, I_C=-2mA$	150	600	
Collector Saturation Voltage	$V_{CE(sat)}$	$I_C=-100mA, I_B=-10mA$		-0.30	V